

PSMN4R1-60YL

N-channel 60 V, 4.1 m Ω logic level MOSFET in LFPAK56 Product data sheet

1. **General description**

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product is designed and qualified for use in a wide range of power supply & motor control equipment.

Features and benefits 2.

- Advanced TrenchMOS provides low R_{DSon} and low gate charge
- Logic level gate operation
- Avalanche rated, 100% tested
- LFPAK provides maximum power density in a Power SO8 package

Applications 3.

- Synchronous rectifier in LLC topology
- Chargers & adaptors with V_{out} < 10 V
- Fast charge & USB-PD applications
- Battery powered motor control
- LED lighting & TV backlight

Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	238	W
Static charact	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 11$		-	3.3	4.8	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 48 V; V _{GS} = 5 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>		-	18.1	-	nC

[1] Continuous current is limited by package.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D I
2	S	source		
3	S	source	[qj	G 4
4	G	gate	وققق	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN4R1-60YL	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	60	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	60	V
V_{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	238	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	100	Α
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>	[1]	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; Fig. 3		-	593	Α
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain o	diode			'		
Is	source current	T _{mb} = 25 °C	[1]	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	593	Α

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Symbol	Parameter	Conditions		Min	Max	Unit
Avalanche rug	gedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 100 A; $V_{sup} \le$ 60 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[2][3]	-	199	mJ

- [1]
- Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175 $^{\circ}\text{C}.$
- Refer to application note AN10273 for further information.

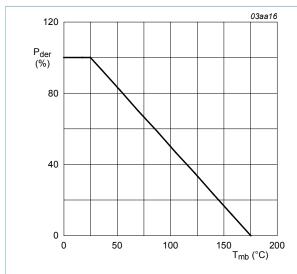
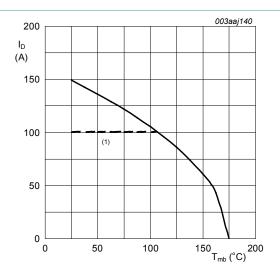


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

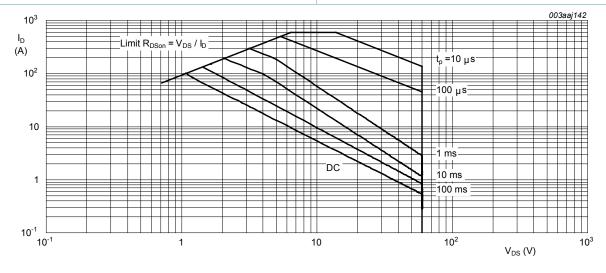
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



(1) Capped at 100A due to package

Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$



Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$$T_{mb}$$
 = 25°C; I_{DM} is a single pulse

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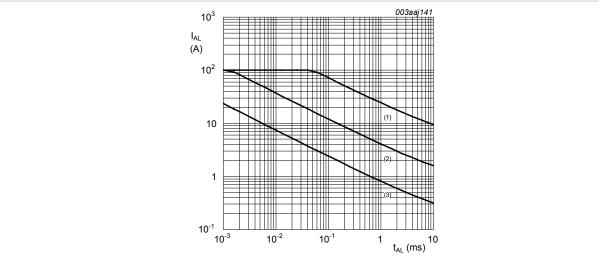


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1)
$$T_{j(init)} = 25$$
°C; (2) $T_{j(init)} = 150$ °C; (3) Repetitive Avalanche

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.63	K/W

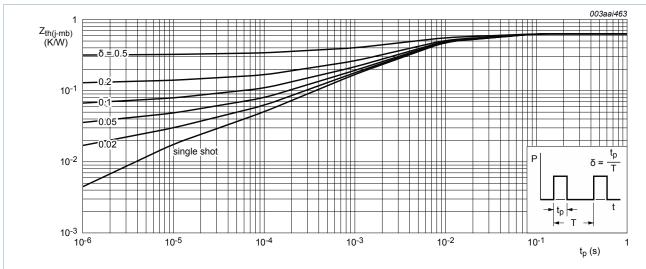


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

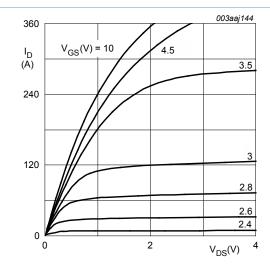
9. Characteristics

Table 6 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		l l			
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	54	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 9$	-	-	2.45	V
		$I_D = 1 \text{ mA; } V_{DS} = V_{GS}; T_j = 175 \text{ °C; } Fig. 9$	0.5	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	0.12	10	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	3.3	4.8	mΩ
resistance	V_{GS} = 10 V; I_{D} = 25 A; T_{j} = 25 °C; Fig. 11	-	2.9	4.1	mΩ	
	V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	10.8	mΩ	
Dynamic cl	haracteristics					
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 48 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	103	-	nC
		I _D = 25 A; V _{DS} = 48 V; V _{GS} = 5 V;	-	54.8	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	13.6	-	nC
Q_{GD}	gate-drain charge		-	18.1	-	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	5890	7853	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	506	607	pF
C _{rss}	reverse transfer capacitance		-	276	378	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 45 \text{ V}; R_L = 1.8 \Omega; V_{GS} = 5 \text{ V};$	-	28	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$; $T_j = 25 °C$	-	53	-	ns
t _{d(off)}	turn-off delay time		-	80	-	ns
t _f	fall time	1	-	47	-	ns
Source-dra	in diode		l l			J
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _i = 25 °C; <u>Fig. 16</u>	-	0.78	1.2	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	_	29	-	ns
Q _r	recovered charge	$V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	28	-	nC



 $T_i = 25 \,^{\circ}\text{C}; t_p = 300 \,\mu\text{s}$

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

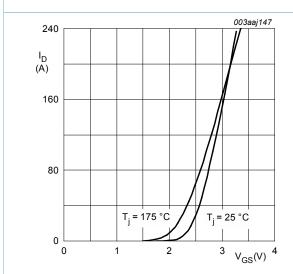


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



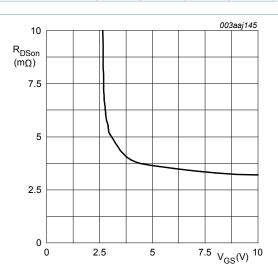


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

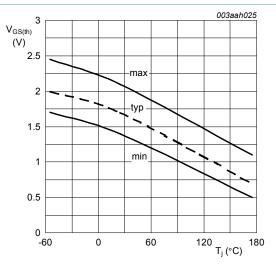


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D$$
 = 1 mA; V_{DS} = V_{GS}

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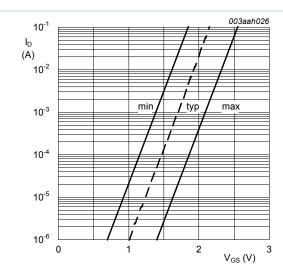


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_i = 25$$
°C; $V_{DS} = 5V$

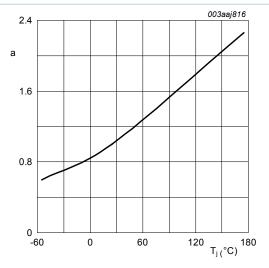
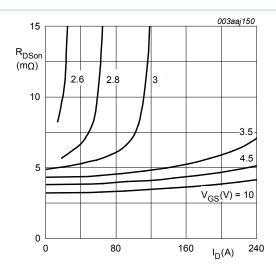


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}C)}$$



$$T_j$$
 = 25 °C; t_p = 300 μ s

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

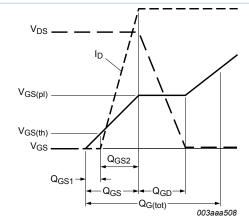


Fig. 13. Gate charge waveform definitions

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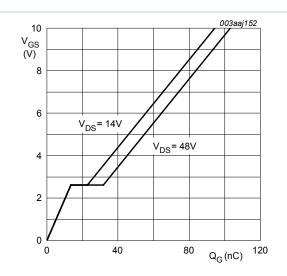


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
°C; $I_D = 25A$

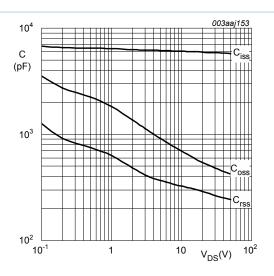


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

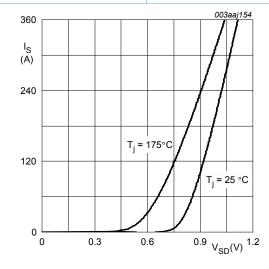


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

10. Package outline

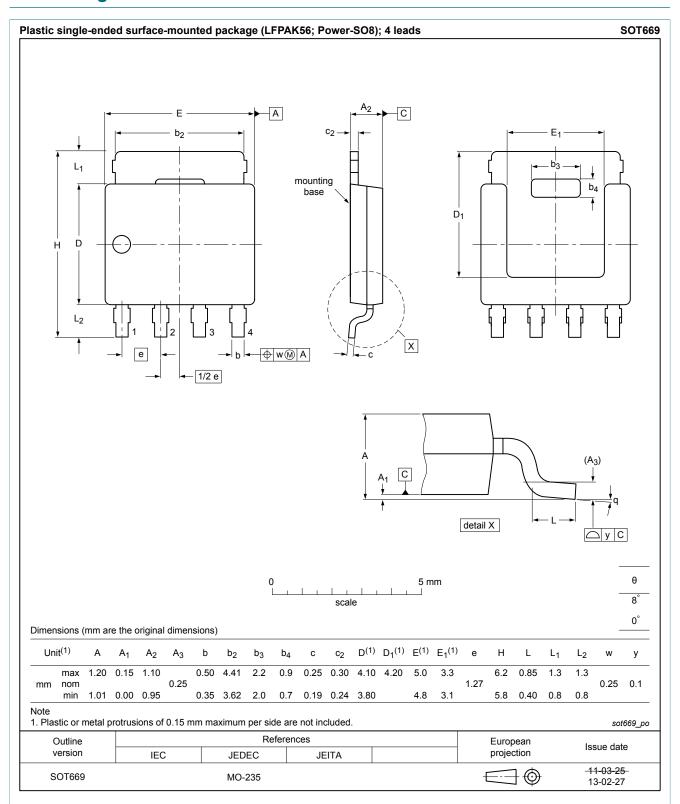


Fig. 17. Package outline LFPAK56; Power-SO8 (SOT669)

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